

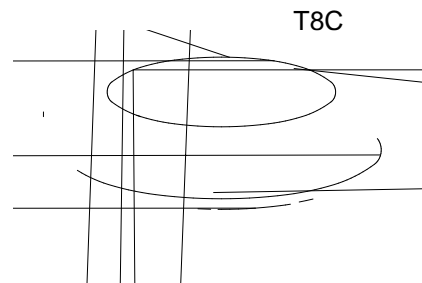
??%\$\$\$!: 5GH GK=H7 <=B ; H<MF=GHCF

%*\$\$J8FA

<=: < DCK9F H<MF=GHCF : CF =BJ9FH9F 5DD@=75H=CB

:YUhiYg.

" 5` 8]ZigYX GhfiWhiY
 " 5 a d`]zm]b[; UhY 7cbZ][ifUh]cb
 " 6`cW_]b[WUdUV`]hm id hc %*\$\$ jc`hg
 " <][\ Xj#Xh 7UdUV`]hm
 " DfYggiY 5ggYaV`YX 8Yj]WY



9@97HF=75@ 7<5F57H9F=GH=7G 5B8 F5H=B ; G

6`cW_]b[! CZZ GhUhY

Device Type	V _{RRM} (1)	V _{DRM} (1)	V _{RSM} (1)
KK1000/16	1600	1600	1800

V_{RRM} = Repetitive peak reverse voltage
 V_{DRM} = Repetitive peak off state voltage
 V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I _{RRM} /I _{DRM}	5 mA 80 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

7cbXiWh]b[! Cb GhUhY

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DUFU a YhYf	Gma Vc`	A]b"	AU1"	Hmd"	I b]hg	7 cbX]h]cbg
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-t						

